



**THE DATASHEET OF  
NTMFS4934NT1G**





## **NTMFS4934N**

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

# NTMFS4934N

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.8	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	46.0	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	134.2	
Junction-to-Ambient – ( $t \leq 10$ s) (Note 3)	$R_{\theta JA}$	17.3	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ $\mu$ A	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			15.2		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^\circ\text{C}$		1.0	$\mu$ A
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			$\pm 100$	nA

### ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250$ $\mu$ A	1.2	1.6	2.2	V	
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.6		mV/°C	
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10$ V	$I_D = 30$ A		1.52	2.0	m $\Omega$
			$I_D = 15$ A		1.52		
		$V_{GS} = 4.5$ V	$I_D = 30$ A		2.2	3.0	
			$I_D = 15$ A		2.2		
Forward Transconductance	$g_{FS}$	$V_{DS} = 1.5$ V, $I_D = 15$ A		80		S	

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = 15$ V		5505		pF
Output Capacitance	$C_{OSS}$			2355		
Reverse Transfer Capacitance	$C_{RSS}$			90		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V; $I_D = 30$ A		34		nC
Threshold Gate Charge	$Q_{G(TH)}$			3.8		
Gate-to-Source Charge	$Q_{GS}$			13.9		
Gate-to-Drain Charge	$Q_{GD}$			8.1		
Total Gate Charge	$Q_{G(TOT)}$		$V_{GS} = 10$ V, $V_{DS} = 15$ V; $I_D = 30$ A		76.5	

### SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5$ V, $V_{DS} = 15$ V, $I_D = 15$ A, $R_G = 3.0$ $\Omega$		20.0		ns
Rise Time	$t_r$			36.2		
Turn-Off Delay Time	$t_{d(OFF)}$			39.3		
Fall Time	$t_f$			9.4		

5. Pulse Test: pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>SWITCHING CHARACTERISTICS</b> (Note 6)						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A},$ $R_G = 3.0\ \Omega$		13.2		ns
Rise Time	$t_r$			33.3		
Turn-Off Delay Time	$t_{d(OFF)}$			49.7		
Fall Time	$t_f$			7.8		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V},$ $I_S = 30\text{ A}$	$T_J = 25^\circ\text{C}$		0.79	1.0	V
			$T_J = 125^\circ\text{C}$		0.66		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$ $I_S = 30\text{ A}$		59.1		ns	
Charge Time	$t_a$			28.3			
Discharge Time	$t_b$			30.8			
Reverse Recovery Charge	$Q_{RR}$			70			nC

## PACKAGE PARASITIC VALUES

Source Inductance	$L_S$	$T_A = 25^\circ\text{C}$		1.00		nH
Drain Inductance	$L_D$			0.005		nH
Gate Inductance	$L_G$			1.84		nH
Gate Resistance	$R_G$			0.80		$\Omega$

5. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

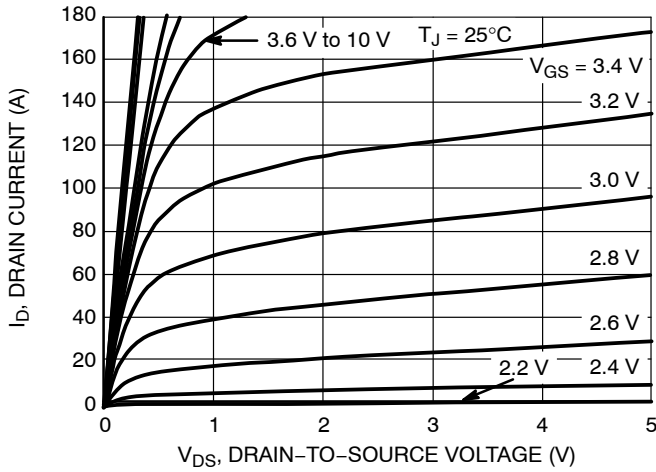


Figure 1. On-Region Characteristics

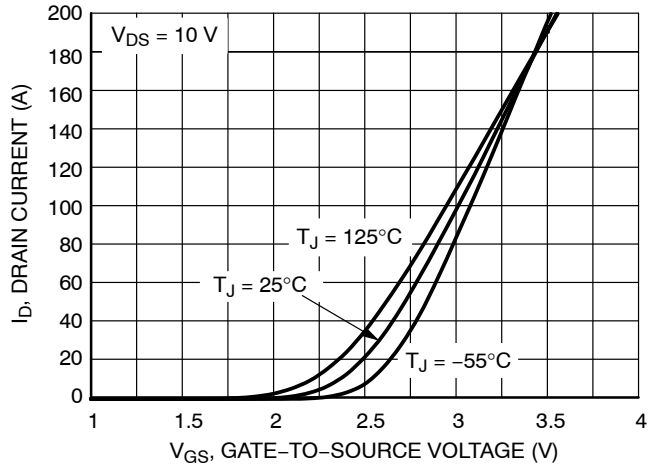


Figure 2. Transfer Characteristics

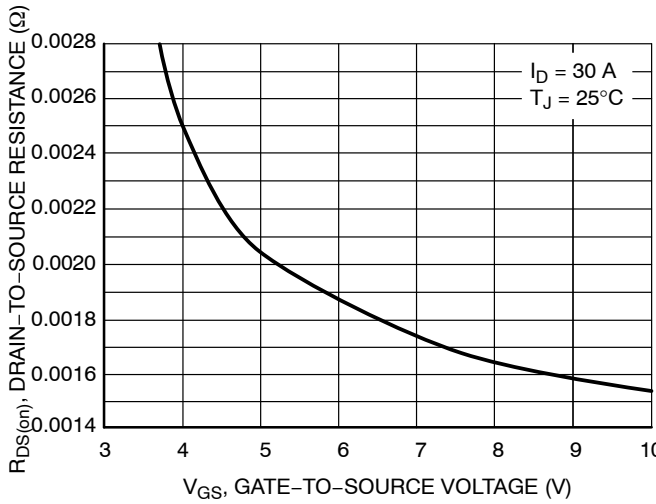


Figure 3. On-Resistance vs. Gate-to-Source Voltage

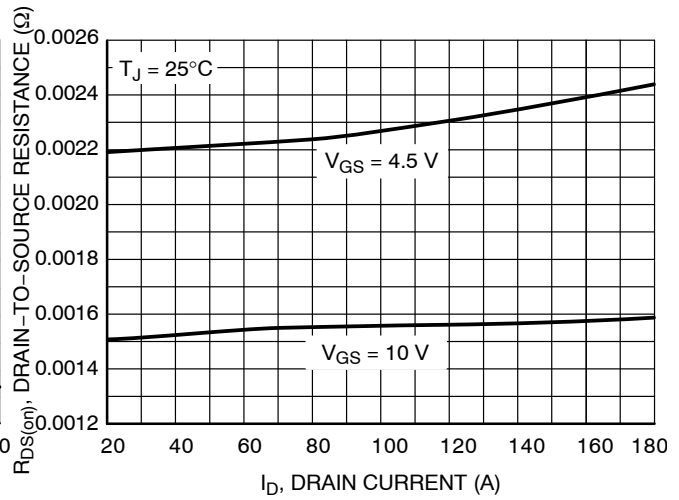


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

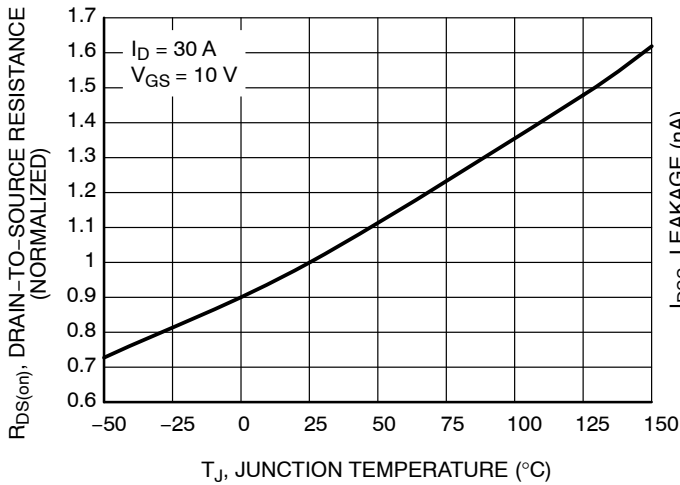


Figure 5. On-Resistance Variation with Temperature

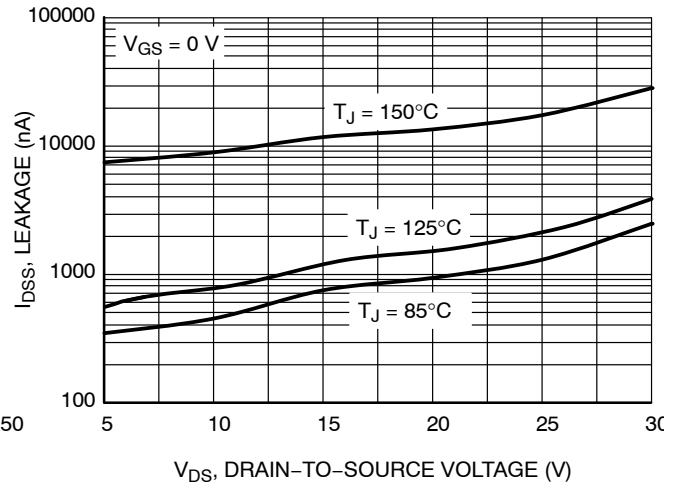


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

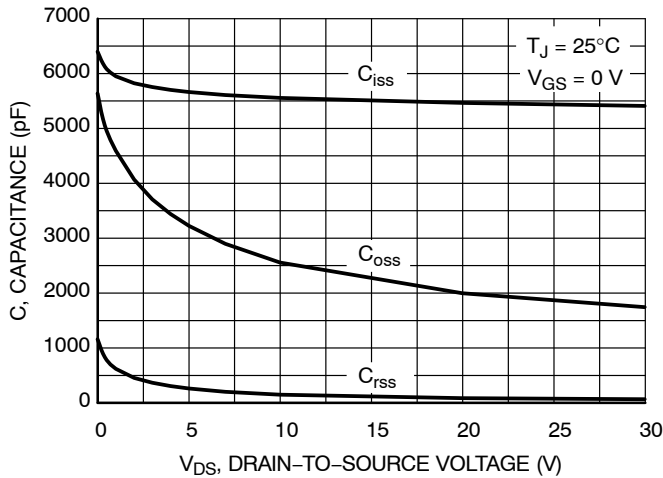


Figure 7. Capacitance Variation

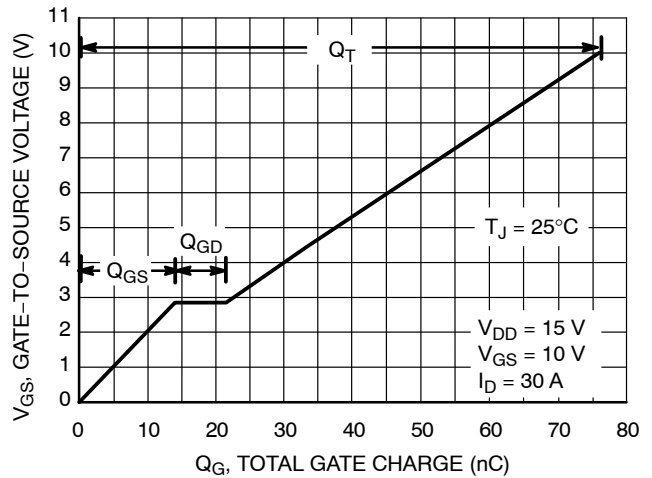


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

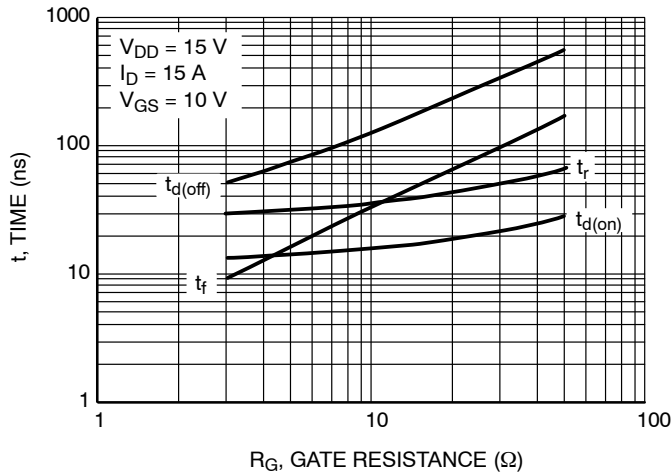


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

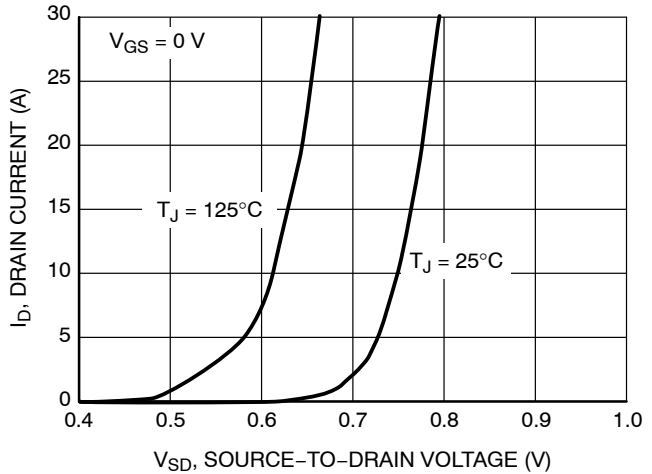


Figure 10. Diode Forward Voltage vs. Current

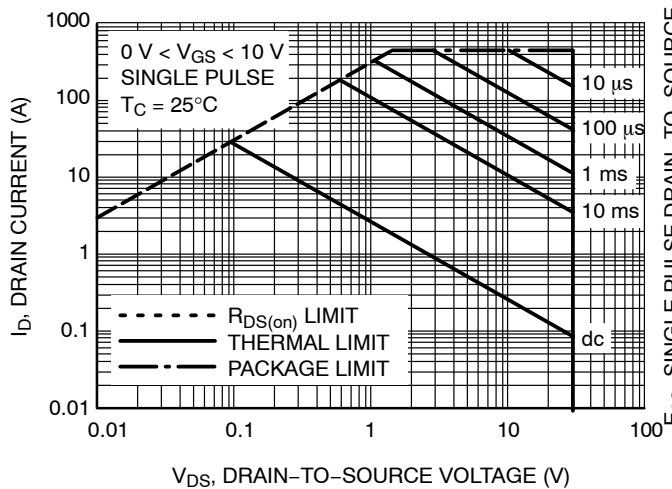


Figure 11. Maximum Rated Forward Biased Safe Operating Area

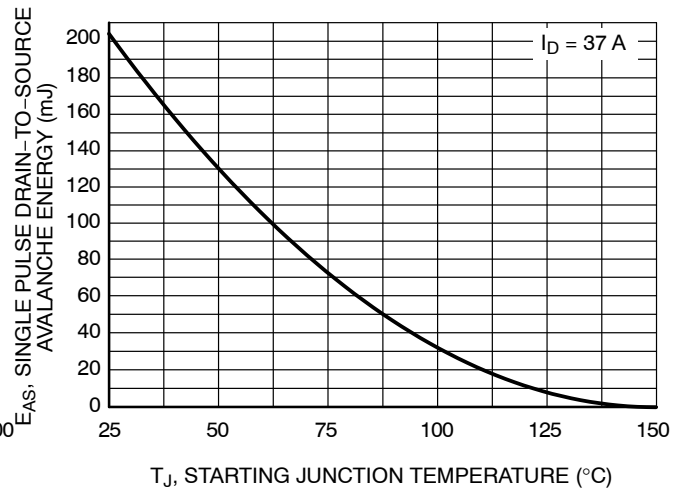


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL CHARACTERISTICS

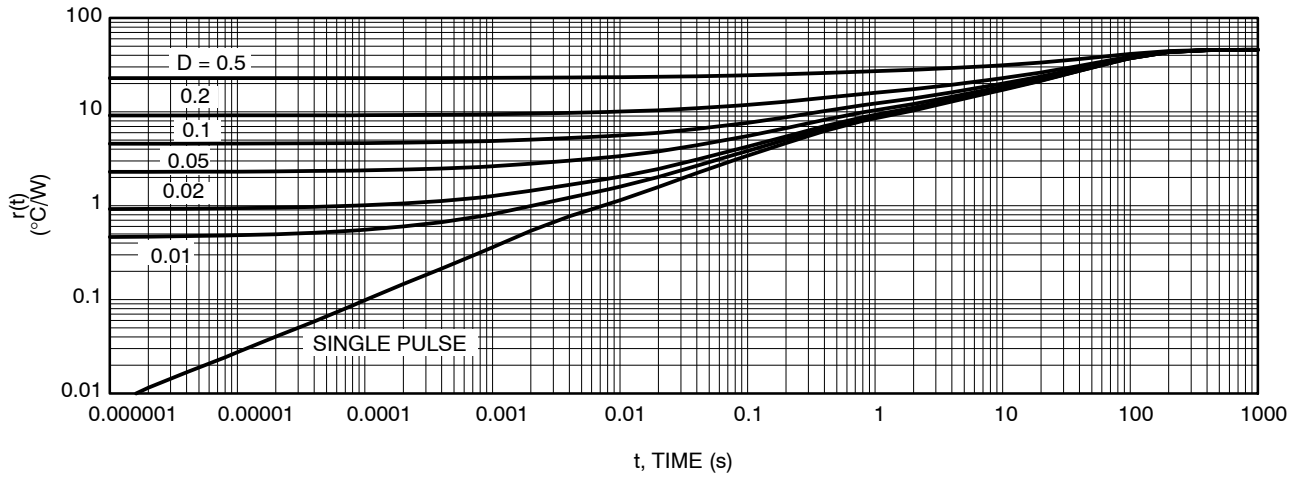


Figure 13. Thermal Response

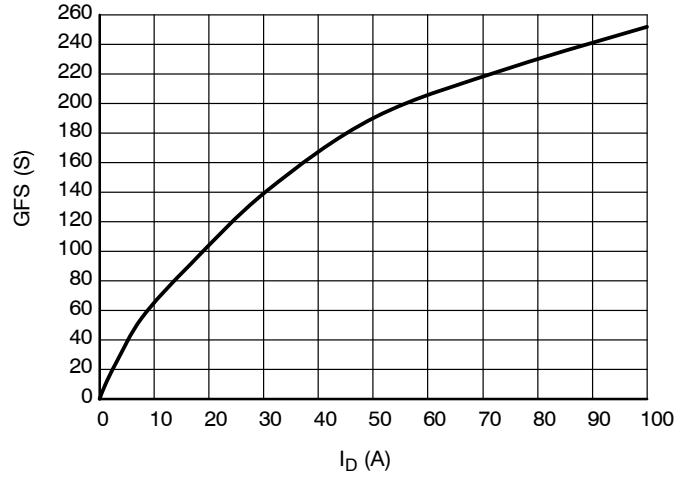
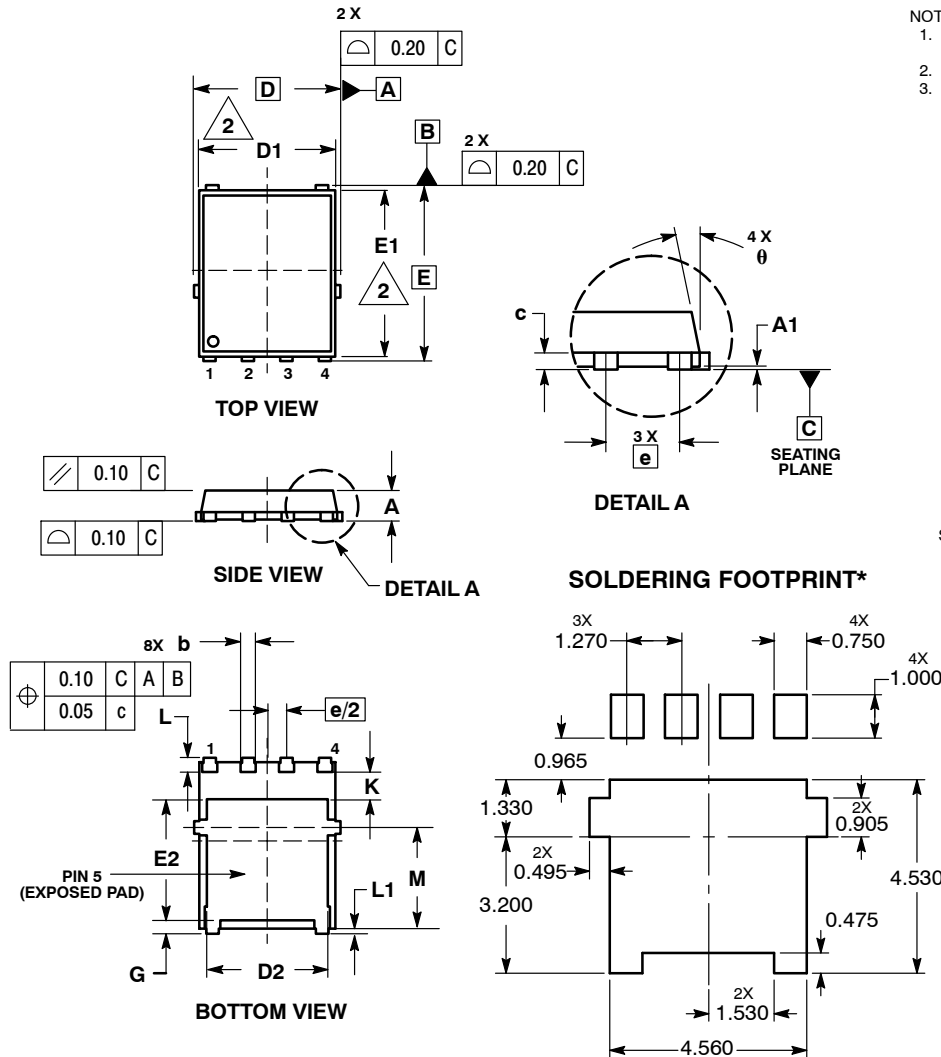


Figure 14. GFS vs.  $I_D$

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## PACKAGE DIMENSIONS

DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE G



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.50	4.90	5.10
D2	3.50	---	4.22
E	6.15 BSC		
E1	5.50	5.80	6.10
E2	3.45	---	4.30
e	1.27 BSC		
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0°	---	12°

- STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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